

SCES294C-OCTOBER 1999-REVISED MAY 2005

FE	ATURES	D		CKAG	-
•	Member of Texas Instruments' Widebus™			VIEW)	<b>E</b>
	Family		<b>—</b> (		
•	UBT™ Transceiver Combines D-Type Latches	1OEAB	1		] CLK
	and D-Type Flip-Flops for Operation in	10EBA	1		1LEAB
	Transparent, Latched, or Clocked Modes	V <sub>CC</sub>			1LEBA
•	TI-OPC™ Circuitry Limits Ringing on	1A1 [			ERC
	Unevenly Loaded Backplanes	GND [	1		GND
•	OEC™ Circuitry Improves Signal Integrity and	1A2 [		-	] 1B1
	Reduces Electromagnetic Interference	1A3 [			1B2
•	Bidirectional Interface Between GTLP Signal	GND [			] GND
	Levels and LVTTL Logic Levels	1A4 [			] 1B3
•	Partitioned as Two 8-Bit Transceivers With	GND [			] 1B4 ] 1B5
-	Individual Latch Timing and Output Control,	1A5 [ GND [			GND
	but With a Common Clock	1A6	1	-	1B6
•	LVTTL Interfaces Are 5-V Tolerant	1A0 [ 1A7 [	1		1B7
•	High-Drive GTLP Outputs (100 mA)	V <sub>cc</sub> [			V <sub>CC</sub>
	LVTTL Outputs (–24 mA/24 mA)	1A8 [			] 1B8
•		2A1 [			2B1
•	Variable Edge-Rate Control (ERC) Input	GND	18	47	GND
	Selects GTLP Rise and Fall Times for Optimal Data-Transfer Rate and Signal Integrity in	2A2 [	19	46	2B2
	Distributed Loads	2A3 [	20	45	2B3
		GND [		44	] GND
•	I <sub>off</sub> , Power-Up 3-State, and BIAS V <sub>CC</sub> Support Live Insertion	2A4 [	1		] 2B4
		2A5 [	1		<b>2</b> B5
•	Bus Hold on A-Port Data Inputs	GND [	1		V <sub>REF</sub>
٠	Distributed V <sub>CC</sub> and GND Pins Minimize	2A6	1	-	2B6
	High-Speed Switching Noise	GND [	1	-	] GND
٠	Latch-Up Performance Exceeds 100 mA Per	2A7 [		-	2B7
	JESD 78, Class II	V <sub>CC</sub>			2B8
٠	ESD Protection Exceeds JESD 22	2A8 [	1		BIAS V <sub>CC</sub>
	– 2000-V Human-Body Model (A114-A)	GND [	1	-	2LEAB
	– 200-V Machine Model (A115-A)		1		] 2LEBA ] <del>OE</del>
	– 1000-V Charged-Device Model (C101)	2 <mark>0EBA</mark> [	32	55	JUE

## DESCRIPTION

The SN74GTLPH1655 is a high-drive, 16-bit UBT™ transceiver that provides LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. It is partitioned as two 8-bit transceivers and allows for transparent, latched, and clocked modes of data transfer. The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTLP signal levels. High-speed (about three times faster than standard LVTTL or TTL) backplane operation is a direct result of GTLP's reduced output swing (<1 V), reduced input threshold levels, improved differential input, OEC<sup>™</sup> circuitry, and TI-OPC<sup>™</sup> circuitry. Improved GTLP OEC and TI-OPC circuits minimize bus-settling time and have been designed and tested using several backplane models. The high drive allows incident-wave switching in heavily loaded backplanes with equivalent load impedance down to 11  $\Omega$ .



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## DESCRIPTION (CONTINUED)

GTLP is the Texas Instruments (TI™) derivative of the Gunning Transceiver Logic (GTL) JEDEC standard JESD 8-3. The ac specification of the SN74GTLPH1655 is given only at the preferred higher noise-margin GTLP, the user of but has the flexibility using this device at either GTL  $(V_{TT} = 1.2 \text{ V and } V_{REF} = 0.8 \text{ V})$  or GTLP  $(V_{TT} = 1.5 \text{ V and } V_{REF} = 1 \text{ V})$  signal levels.

Normally, the B port operates at GTLP signal levels. The A-port and control inputs operate at LVTTL logic levels, but are 5-V tolerant and are compatible with TTL and 5-V CMOS inputs.  $V_{REF}$  is the B-port differential input reference voltage.

This device is fully specified for live-insertion applications using  $I_{off}$ , power-up 3-state, and BIAS  $V_{CC}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict. The BIAS  $V_{CC}$  circuitry precharges and preconditions the B-port input/output connections, preventing disturbance of active data on the backplane during card insertion or removal, and permits true live-insertion capability.

This GTLP device features TI-OPC circuitry, which actively limits overshoot caused by improperly terminated backplanes, unevenly distributed cards, or empty slots during low-to-high signal transitions. This improves signal integrity, which allows adequate noise margin to be maintained at higher frequencies.

High-drive GTLP backplane interface devices feature adjustable edge-rate control (ERC). Changing the ERC input voltage between GND and  $V_{CC}$  adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load.

Active bus-hold circuitry holds unused or undriven LVTTL data inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

When  $V_{CC}$  is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, the output-enable ( $\overline{OE}$ ) input should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

#### **ORDERING INFORMATION**

T <sub>A</sub>	PACKAGE <sup>(1)</sup>		ORDERABLE PART NUMBER	TOP-SIDE MARKING	
–40°C to 85°C	TSSOP – DGG	Tape and reel	SN74GTLPH1655DGGR	GTLPH1655	

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

## FUNCTIONAL DESCRIPTION

The SN74GTLPH1655 is a high-drive (100 mA), 16-bit UBT transceiver containing D-type latches and D-type flip-flops for data-path operation in transparent, latched, or clocked modes. The device is uniquely partitioned as two 8-bit transceivers with individual latch timing and output signals and a common clock for both transceiver words. It can replace any of the functions shown in Table 1. Data polarity is noninverting.

Table 1. SN/4G1LPH1055 UB1 Transceiver Replacement Function	le 1. SN74GTLPH1655 UBT Transceiver Rep	<b>lacement Functions</b>
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FUNCTION	8 BIT	9 BIT	10 BIT	16 BIT			
Transceiver	'245, '623, '645	'863	'861	'16245, '16623			
Buffer/driver	'241, '244, '541		'827	'16241, '16244, '16541			
Latched transceiver	'543			'16543			
Latch	'373, '573	'843	'841	'16373			
Registered transceiver	'646, '652			'16646, '16652			
Flip-flop	'374, '574		'821	'16374			
SN74GTLPH1655 UBT transceiver replaces all above functions							

## FUNCTIONAL DESCRIPTION (CONTINUED)

Data flow for each word is determined by the respective latch enables (xLEAB and xLEBA), output enables (xOEAB and xOEBA), and clock (CLK). The output enables (1OEAB, 1OEBA, 2OEAB, and 2OEBA) control byte 1 and byte 2 data for the A-to-B and B-to-A directions, respectively. Note that CLK is common to both directions and both 8-bit words. OE also is common and disables all I/O ports simultaneously.

For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB transitions low, the A data is latched independent of CLK high or low. If LEAB is low, the A data is registered on the CLK low-to-high transition. When OEAB is low, the outputs are active. With OEAB high, the outputs are in the high-impedance state.

The data flow for the B-to-A direction is identical, except OEBA, LEBA, and CLK are used.

FUNCTION								
	INP	UTS		OUTPUT	MODE			
OEAB	LEAB	CLK	Α	В	MODE			
Н	Х	Х	Х	Z	Isolation			
L	L	Н	Х	B <sub>0</sub> <sup>(2)</sup>	Latabad stars as of A data			
L	L	L	Х	B <sub>0</sub> <sup>(3)</sup>	Latched storage of A data			
L	Н	Х	L	L				
L	Н	Х	Н	Н	True transparent			
L	L	Ŷ	L	L				
L	L	$\uparrow$	Н	н	Clocked storage of A data			
l								

# FUNCTION TABLES

(1) A-to-B data flow is shown. B-to-A flow is similar, but uses OEBA, LEBA, and CLK. The condition when OEAB and OEBA are both low at the same time is not recommended.

(2) Output level before the indicated steady-state input conditions were established, provided that CLK was high before LEAB went low

(3) Output level before the indicated steady-state input conditions were established

#### OUTPUT ENABLE

	INPUTS	OUTPUTS		
OE	OE OEAB		A PORT	B PORT
L	L	L	Active	Active <sup>(1)</sup>
L	L	Н	Z	Active
L	Н	L	Active	Z
L	Н	Н	Z	Z
Н	Х	Х	Z	Z

(1) This condition is not recommended.

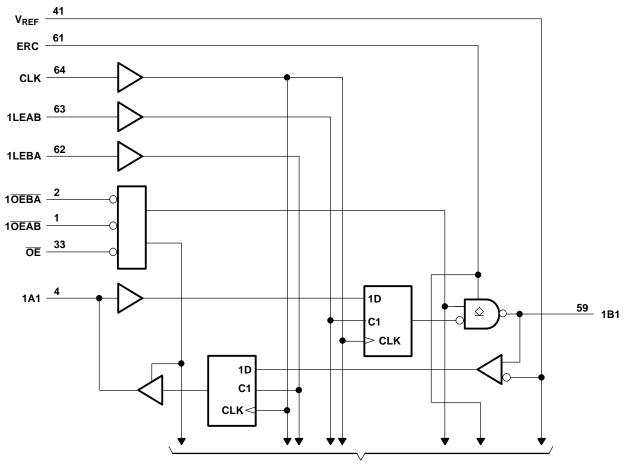
#### B-PORT EDGE-RATE CONTROL (ERC)

INPU	T ERC	OUTPUT
LOGIC LEVEL	NOMINAL VOLTAGE	B-PORT EDGE RATE
Н	V <sub>CC</sub>	Slow
L	GND	Fast

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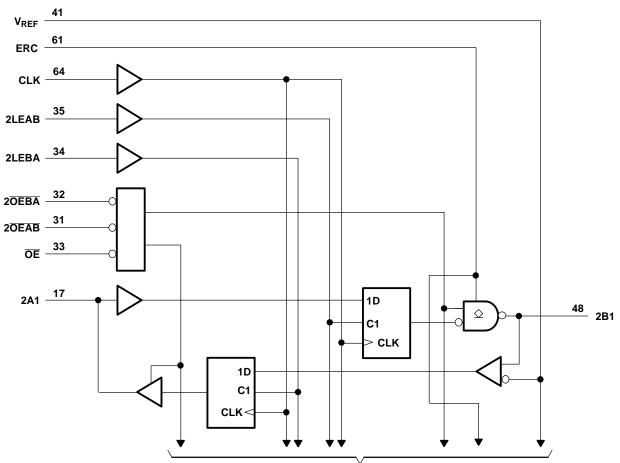
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LOGIC DIAGRAM (POSITIVE LOGIC)



To Seven Other Channels

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## LOGIC DIAGRAM (POSITIVE LOGIC) (CONTINUED)

To Seven Other Channels

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## Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V <sub>CC</sub> BIAS V <sub>CC</sub>	Supply voltage range				V
VI	Input voltage range <sup>(2)</sup>	A port, ERC, and control inputs	-0.5	7	V
۷I	Input voltage range <sup>(2)</sup>	B port and V <sub>REF</sub>	-0.5	4.6	v
V	Voltage range applied to any output	A port	-0.5	7	V
Vo	in the high-impedance or power-off state <sup>(2)</sup>	B port	-0.5	4.6	v
	Current into any output in the low state	A port		48	
lo		B port		200	mA
I <sub>O</sub>	Current into any A-port output in the high state <sup>(3)</sup>			48	mA
	Continuous current through each $V_{CC}$ or GND			±100	mA
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-50	mA
I <sub>ОК</sub>	Output clamp current	V <sub>O</sub> < 0		-50	mA
$\theta_{JA}$	Package thermal impedance <sup>(4)</sup>			55	°C/W
T <sub>stg</sub>	Storage temperature range	-65	150	°C	

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed. (2)

(3) This current flows only when the output is in the high state and  $V_O > V_{CC}$ . (4) The package thermal impedance is calculated in accordance with JESD 51-7.

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# Recommended Operating Conditions<sup>(1)(2)(3)(4)</sup>

			MIN	NOM	MAX	UNIT
V <sub>CC</sub> , BIAS V <sub>CC</sub>	Supply voltage		3.15	3.3	3.45	V
V	Termination voltage	GTL	1.14	1.2	1.26	V
V <sub>TT</sub>	Termination voltage	GTLP	1.35	1.5	1.65	v
V	Poforonoo voltogo	GTL	0.74	0.8	0.87	V
V <sub>REF</sub>	Reference voltage	GTLP	0.87	1	1.1	v
M	Input voltage	B port			V <sub>TT</sub>	V
VI	input voitage	Except B port		$V_{CC}$	5.5	v
	High-level input voltage	B port	V <sub>REF</sub> + 0.05			
V <sub>IH</sub>		ERC	$V_{CC} - 0.6$	V <sub>CC</sub>	5.5	V
		Except B port and ERC	2			
	Low-level input voltage	B port			V <sub>REF</sub> – 0.05	
V <sub>IL</sub>		ERC		GND	0.6	V
		Except B port and ERC			0.8	
I <sub>IK</sub>	Input clamp current				–18	mA
I <sub>OH</sub>	High-level output current	A port			-24	mA
		A port			24	
I <sub>OL</sub>	Low-level output current	B port			100	mA
Δt/Δv	Input transition rise or fall rate	Outputs enabled			10	ns/V
$\Delta t / \Delta V_{CC}$	Power-up ramp rate		20			μs/V
T <sub>A</sub>	Operating free-air temperature		-40		85	°C

(1) All unused control and B-port inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI

application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004. Proper connection sequence for use of the B-port I/O precharge feature is GND and BIAS  $V_{CC} = 3.3 V$  first, I/O second, and  $V_{CC} = 3.3 V$  last, because the BIAS  $V_{CC}$  precharge circuitry is disabled when any  $V_{CC}$  pin is connected. The control and  $V_{REF}$  inputs can be connected anytime, but normally are connected during the I/O stage. If B-port precharge is not required, any connection sequence is (2) acceptable, but generally, GND is connected first.

(3)

 $V_{TT}$  and  $R_{TT}$  can be adjusted to accommodate backplane impedances if the dc recommended I<sub>OL</sub> ratings are not exceeded.  $V_{REF}$  can be adjusted to optimize noise margins, but normally is two-thirds  $V_{TT}$ . TI-OPC circuitry is enabled in the A-to-B direction and is activated when  $V_{TT} > 0.7$  V above  $V_{REF}$ . If operated in the A-to-B direction,  $V_{REF}$  should be set to within 0.6 V of  $V_{TT}$  to minimize current (4) drain.

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#### **Electrical Characteristics**

over recommended operating free-air temperature range for GTLP (unless otherwise noted)

PARAMETER V <sub>IK</sub>		ARAMETERTEST CONDITIONS $V_{CC} = 3.15 \text{ V},$ $I_{j} = -18 \text{ mA}$		MIN	TYP <sup>(1)</sup>	MAX	UNIT	
						-1.2	V	
		V <sub>CC</sub> = 3.15 V to 3.45 V,	I <sub>OH</sub> = −100 μA	$V_{CC} - 0.2$				
V <sub>OH</sub>	A port		I <sub>OH</sub> = -12 mA	2.4			V	
		V <sub>CC</sub> = 3.15 V	I <sub>OH</sub> = -24 mA	2				
		V <sub>CC</sub> = 3.15 V to 3.45 V,	I <sub>OL</sub> = 100 μA			0.2		
	A port	V 245V	I <sub>OL</sub> = 12 mA			0.4		
V		V <sub>CC</sub> = 3.15 V	I <sub>OL</sub> = 24 mA			0.5	V	
V <sub>OL</sub>			I <sub>OL</sub> = 10 mA			0.2	v	
	B port	V <sub>CC</sub> = 3.15 V	I <sub>OL</sub> = 64 mA			0.4		
				I <sub>OL</sub> = 100 mA			0.55	
l <sub>l</sub>	Control inputs	V <sub>CC</sub> = 3.45 V,	V <sub>I</sub> = 0 or 5.5 V			±10	μA	
. (2)	A port	– V <sub>CC</sub> = 3.45 V	$V_{O} = V_{CC}$			10		
I <sub>OZH</sub> <sup>(2)</sup>	B port	$V_{\rm CC} = 3.45 \text{ V}$	V <sub>O</sub> = 1.5 V			10	μA	
I <sub>OZL</sub> <sup>(2)</sup>	A and B ports	V <sub>CC</sub> = 3.45 V,	V <sub>O</sub> = GND			-10	μA	
I <sub>BHL</sub> <sup>(3)</sup>	A port	V <sub>CC</sub> = 3.15 V,	V <sub>I</sub> = 0.8 V	75			μA	
I <sub>BHH</sub> <sup>(4)</sup>	A port	V <sub>CC</sub> = 3.15 V,	V <sub>1</sub> = 2 V	-75			μA	
I <sub>BHLO</sub> <sup>(5)</sup>	A port	V <sub>CC</sub> = 3.45 V,	$V_{I} = 0$ to $V_{CC}$	500			μA	
I <sub>BHHO</sub> <sup>(6)</sup>	A port	V <sub>CC</sub> = 3.45 V,	$V_{I} = 0$ to $V_{CC}$	-500			μA	
		$V_{\rm CC} = 3.45 \text{ V}, I_{\rm O} = 0,$	Outputs high			40		
I <sub>CC</sub>	A or B port	$V_{I}$ (A-port or control input) = $V_{CC}$ or GND,	Outputs low			40	mA	
		$V_{I}$ (B port) = $V_{TT}$ or GND	Outputs disabled			40		
$\Delta I_{CC}^{(7)}$		$V_{CC}$ = 3.45 V, One A-port or control input at Other A-port or control inputs at $V_{CC}$ or GNI				1.5	mA	
C <sub>i</sub>	Control inputs	V <sub>I</sub> = 3.15 V or 0			4.5	6.5	pF	
<u> </u>	A port	V <sub>O</sub> = 3.15 V or 0			6.5	7.5	۶Ē	
C <sub>io</sub>	B port $V_0 = 1.5 \text{ V or } 0$				8.5	10.5	pF	

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 All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.
For I/O ports, the parameters I<sub>OZH</sub> and I<sub>OZL</sub> include the input leakage current.
The bus-hold circuit can sink at least the minimum low sustaining current at V<sub>IL</sub>max. I<sub>BHL</sub> should be measured after lowering V<sub>IN</sub> to GND and then raising it to  $V_{\text{IL}}\text{max}.$ 

(4) The bus-hold circuit can source at least the minimum high sustaining current at VIHmin. IBHH should be measured after raising VIN to VCC and then lowering it to  $V_{\mbox{\scriptsize IH}}\mbox{min}.$ 

(5)

(6)

An external driver must source at least  $I_{BHLO}$  to switch this node from low to high. An external driver must sink at least  $I_{BHHO}$  to switch this node from high to low. This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V<sub>CC</sub> or GND. (7)

## **Hot-Insertion Specifications for A Port**

over operating free-air temperature range

PARAMETER		TEST CONDITIONS			UNIT
I <sub>off</sub>	$V_{CC} = 0,$	BIAS $V_{CC} = 0$ ,	$V_{I}$ or $V_{O}$ = 0 to 5.5 V	10	μA
I <sub>OZPU</sub>	$V_{CC} = 0$ to 1.5 V,	$V_{O} = 0.5 V$ to 3 V,	$\overline{OE} = 0$	±30	μA
I <sub>OZPD</sub>	$V_{CC} = 1.5 V \text{ to } 0,$	$V_{O} = 0.5 V$ to 3 V,	$\overline{OE} = 0$	±30	μA

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## Live-Insertion Specifications for B Port

over operating free-air temperature range

PARAMETER		TEST CONDITIONS				UNIT
l <sub>off</sub>	$V_{CC} = 0,$	BIAS $V_{CC} = 0$ ,	$V_1 \text{ or } V_0 = 0 \text{ to } 1.5 \text{ V}$		10	μA
I <sub>OZPU</sub>	$V_{CC} = 0$ to 1.5 V,	BIAS $V_{CC} = 0$ ,	$V_{O} = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μA
I <sub>OZPD</sub>	V <sub>CC</sub> = 1.5 V to 0,	BIAS $V_{CC} = 0$ ,	$V_{O} = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μA
	V <sub>CC</sub> = 0 to 3.15 V	- BIAS $V_{CC}$ = 3.15 V to 3.45 V,	$V_O$ (B port) = 0 to 1.5 V		5	mA
I <sub>CC</sub> (BIAS V <sub>CC</sub> )	$V_{CC}$ = 3.15 V to 3.45 V				10	μA
Vo	$V_{CC} = 0,$	BIAS $V_{CC}$ = 3.3 V	$I_{O} = 0$	0.95	1.05	V
Ι <sub>Ο</sub>	$V_{CC} = 0,$	BIAS $V_{CC}$ = 3.15 V to 3.45 V,	V <sub>O</sub> (B port) = 0.6 V	-1		μA

## **Timing Requirements**

over recommended ranges of supply voltage and operating free-air temperature,

 $V_{TT} = 1.5$  V and  $V_{REF} = 1$  V for GTLP (unless otherwise noted)

			MIN	MAX	UNIT
f <sub>clock</sub>	Clock frequency			175	MHz
t <sub>w</sub>	LEAB or LEBA high		3		
	Pulse duration	CLK high or low	3		ns
		A before CLK	3		
	Setup time	B before CLK	3		~~
t <sub>su</sub>		A before LEAB $\downarrow$ , CLK = don't care	2.5	.5	ns
		B before LEBA↓, CLK = don't care	2.5		
		A after CLK	0.5		
t <sub>h</sub>		B after CLK 0.5			
	Hold time	A after LEAB $\downarrow$ , CLK = don't care	0.5		ns
		B after LEBA $\downarrow$ , CLK = don't care	0.5		

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#### **Switching Characteristics**

over recommended ranges of supply voltage and operating free-air temperature,  $V_{TT} = 1.5$  V and  $V_{REF} = 1$  V for GTLP (see Figure 1)

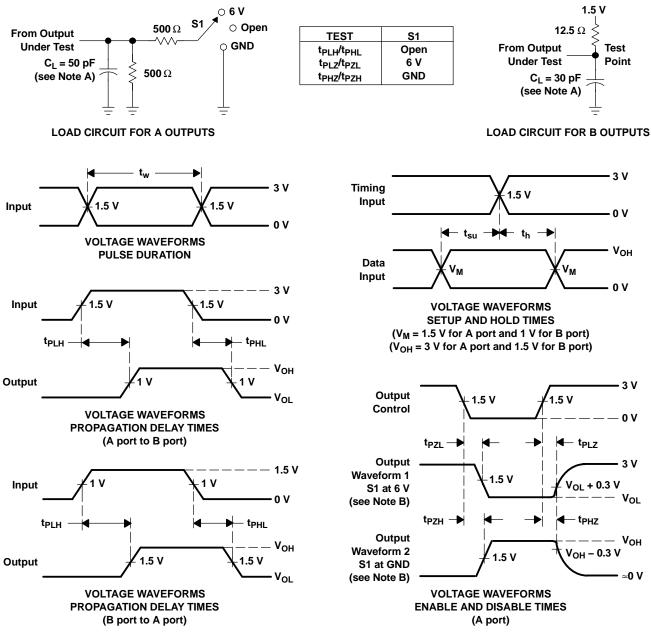
PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE <sup>(1)</sup>	MIN	TYP <sup>(2)</sup> MAX	UNIT	
f <sub>max</sub>				175		MHz	
t <sub>PLH</sub>	A	В	Slow	3.5	7.7	ns	
t <sub>PHL</sub>	Λ	D	5100	2.4	6.3	115	
t <sub>PLH</sub>	А	В	Fast	2	6.3	ns	
t <sub>PHL</sub>	Λ	D	1 431	2	5.9	115	
t <sub>PLH</sub>	LEAB	В	Slow	3.5	7.8	ns	
t <sub>PHL</sub>	LLAD		5100	2.7	6.4	115	
t <sub>PLH</sub>	LEAB	В	Fast	2	6.4	ns	
t <sub>PHL</sub>	LLAD	D	1 431	2	6	115	
t <sub>PLH</sub>	CLK	В	Slow	4.7	8	ns	
t <sub>PHL</sub>	GER	В	310W	2.7	6.4	115	
t <sub>PLH</sub>	CLK	В	Fact	3.6	6.8	nc	
t <sub>PHL</sub>	ULK	CLK B Fast		2	6.1	ns	
t <sub>en</sub>	ŌE B		Clow	3.5	7.3	-	
t <sub>dis</sub>			Slow	3.5	7	ns	
t <sub>en</sub>	ŌĒ	5	Fred	2	6	ns	
t <sub>dis</sub>	ÛE	В	Fast	2	6.6		
t <sub>en</sub>	OEAB	P			7.4		
t <sub>dis</sub>	OEAB	В	Slow	3.5	7	ns	
t <sub>en</sub>	OEAB	P	Fast	2	6.1		
t <sub>dis</sub>	OEAB	В	Fast	2	6.3	ns 3	
			Slow		2.6		
t <sub>r</sub>	Rise time, B outp	uts (20% to 80%)	Fast		ns		
		(222)	Slow		3	1	
t <sub>f</sub>	Fall time, B outp	uts (80% to 20%)	Fast		2.2	ns	
t <sub>PLH</sub>	5	•		1.5	5.5		
t <sub>PHL</sub>	В	A		1.5	5.5	ns	
t <sub>PLH</sub>		•		1.3	5.2		
t <sub>PHL</sub>	LEBA	A		1	5	ns	
t <sub>PLH</sub>	01.11			1.2	6.3		
t <sub>PHL</sub>	CLK	A		1	5	ns	
t <sub>en</sub>	~=			1.5	5.6		
t <sub>dis</sub>	ŌĒ	A		1.5	6.1	ns	
t <sub>en</sub>				1.2	5.4		
t <sub>dis</sub>	OEBA	А		2	6.1	ns	

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## PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control.

- Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\approx$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>r</sub>  $\approx$  2 ns, t<sub>f</sub>  $\approx$  2 ns.

D. The outputs are measured one at a time, with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms



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## DISTRIBUTED-LOAD BACKPLANE SWITCHING CHARACTERISTICS

The preceding switching characteristics table shows the switching characteristics of the device into a lumped load (Figure 1). However, the designer's backplane application probably is a distributed load. The physical representation is shown in Figure 2. This backplane, or distributed load, can be approximated closely to a resistor inductance capacitance (RLC) circuit, as shown in Figure 3. This device has been designed for optimum performance in this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.

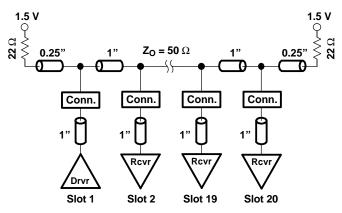


Figure 2. High-Drive Test Backplane

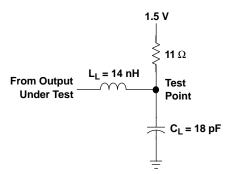


Figure 3. High-Drive RLC Network

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## **Switching Characteristics**

over recommended ranges of supply voltage and operating free-air temperature,  $V_{TT} = 1.5$  V and  $V_{REF} = 1$  V for GTLP (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE <sup>(1)</sup>	TYP <sup>(2)</sup>	UNIT
t <sub>PLH</sub>	۸	В	Clow	5	20
t <sub>PHL</sub>	A	D	Slow	5	ns
t <sub>PLH</sub>	A	В	Fast	3.8	ns
t <sub>PHL</sub>	~	B	T doi	3.8	115
t <sub>PLH</sub>	LEAB	В	Slow	4.9	20
t <sub>PHL</sub>	LLAD	В	Slow	4.9	ns
t <sub>PLH</sub>	LEAB	В	Fast	3.9	ns
t <sub>PHL</sub>	LLAD	В	T doi	3.9	
t <sub>PLH</sub>	CLK	В	Slow	4.8	ns
t <sub>PHL</sub>	OLK	В	Siow	4.8	
t <sub>PLH</sub>	CLK	В	Fast	3.7	ns
t <sub>PHL</sub>	OER		1 431	3.7	
t <sub>en</sub>	OEAB or OE	В	Slow	4.9	ns
t <sub>dis</sub>			Clow	4.7	
t <sub>en</sub>	OEAB or OE	В	Fast	3.5	ns
t <sub>dis</sub>		D	1 431	4.1	
tr	Rise time Route	outs (20% to 80%)	Slow	2	ns
ч			Fast	1.2	113
t <sub>f</sub>	Fall time. B outp	uts (80% to 20%)	Slow	2.5	ne
Ч			Fast	1.8	ns

Slow (ERC = V<sub>CC</sub>) and Fast (ERC = GND) All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C. All values are derived from TI-SPICE models. (1) (2)



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## **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Peak Temp <sup>(3)</sup>	Samples (Requires Login)
74GTLPH1655DGGRE4	ACTIVE	TSSOP	DGG	64	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
74GTLPH1655DGGRG4	ACTIVE	TSSOP	DGG	64	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74GTLPH1655DGGR	ACTIVE	TSSOP	DGG	64	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

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the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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# PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION

#### REEL DIMENSIONS

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TAPE AND REEL INFORMATION

#### TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74GTLPH1655DGGR	TSSOP	DGG	64	2000	330.0	24.4	8.4	17.3	1.7	12.0	24.0	Q1

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# PACKAGE MATERIALS INFORMATION

14-Jul-2012



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74GTLPH1655DGGR	TSSOP	DGG	64	2000	367.0	367.0	45.0

# **MECHANICAL DATA**

MTSS003D - JANUARY 1995 - REVISED JANUARY 1998

### DGG (R-PDSO-G\*\*)

## PLASTIC SMALL-OUTLINE PACKAGE

**48 PINS SHOWN** 



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-153



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